

# MTM765200LBF

Dual N-channel MOSFET

For switching

■ Features

- Low drain-source ON resistance:RDS(on)typ = 80 mΩ (VGS = 4.0 V)
- Low drive voltage: 1.8 V drive
- Halogen-free / RoHS compliant  
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: JA

■ Basic Part Number

Dual Nch MOS 20 V (Individual)

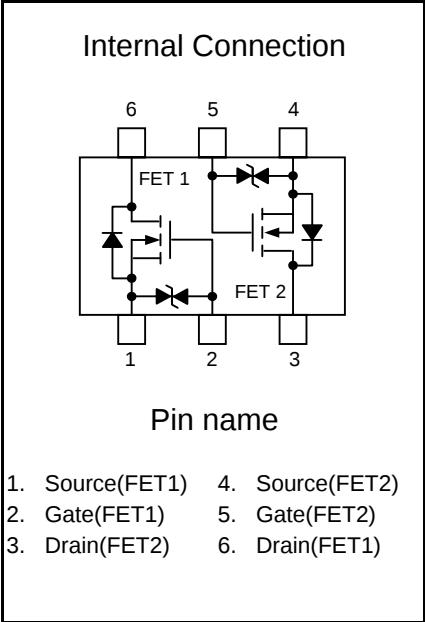
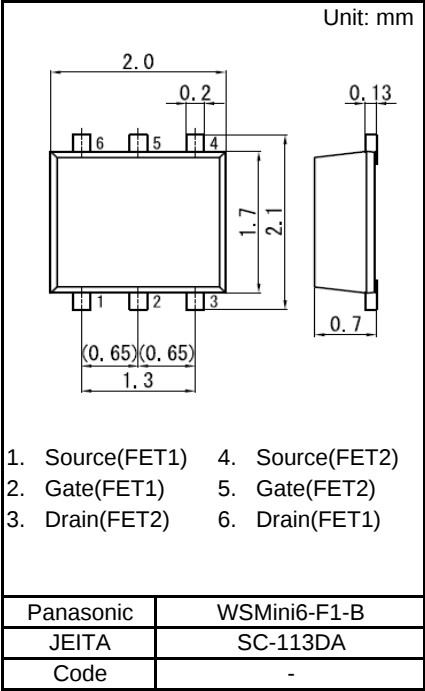
■ Packaging

MTM765200LBF Embossed type (Thermo-compression sealing):  
3 000 pcs / reel (standard)

■ Absolute Maximum Ratings    Ta = 25 °C

| Parameter    |                                      | Symbol            | Rating      | Unit |
|--------------|--------------------------------------|-------------------|-------------|------|
| FET1<br>FET2 | Drain-source Voltage                 | VDS               | 20          | V    |
|              | Gate-source Voltage                  | VGS               | ±10         | V    |
|              | Drain Current                        | ID                | 2.0         | A    |
|              | Drain Current (Pulsed) <sup>*1</sup> | IDp               | 12          | A    |
| Overall      | Total power dissipation              | PD1 <sup>*2</sup> | 700         | mW   |
|              |                                      | PD2 <sup>*3</sup> | 150         |      |
|              | Channel temperature                  | Tch               | 150         | °C   |
|              | Storage temperature                  | Tstg              | -55 to +150 | °C   |

- Note:    \*1    t = 10 μs, Duty Cycle ≤ 1 %  
          \*2    Glass epoxy board ( 25.4 × 25.4 × t0.8 mm ) coated with  
                  copper foil, which has more than 300 mm<sup>2</sup>  
          \*3    Non-heat sink



■ Electrical Characteristics Ta = 25 °C ± 3 °C

FET1,2

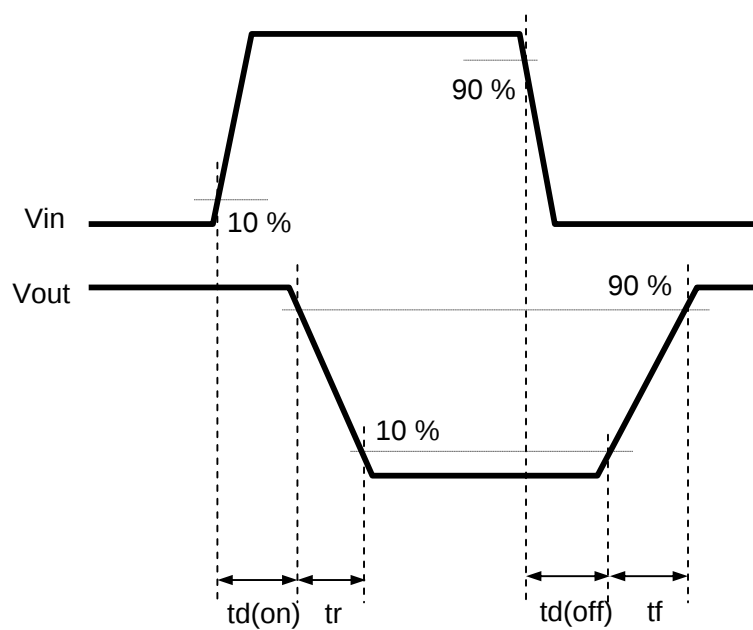
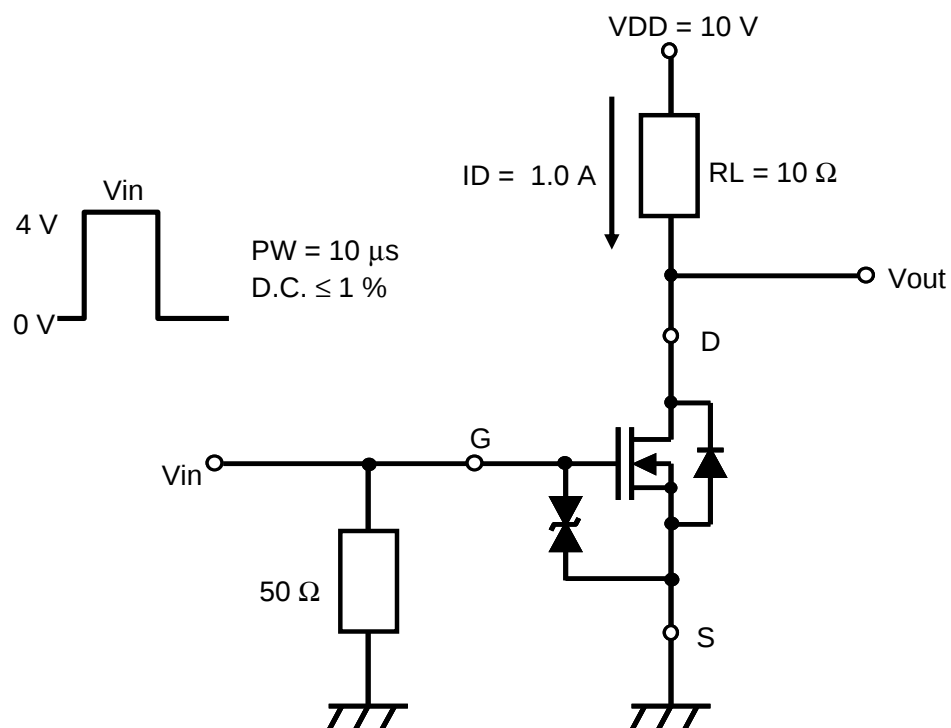
| Parameter                                      | Symbol   | Conditions                                | Min | Typ  | Max | Unit |
|------------------------------------------------|----------|-------------------------------------------|-----|------|-----|------|
| Drain-source Breakdown Voltage                 | VDSS     | ID = 1.0 mA, VGS = 0 V                    | 20  |      |     | V    |
| Zero Gate Voltage Drain Current                | IDSS     | VDS = 20 V, VGS = 0 V                     |     |      | 1.0 | μA   |
| Gate-source Leakage Current                    | IGSS     | VGS = ± 8.0 V, VDS = 0 V                  |     |      | ±10 | μA   |
| Gate-source Threshold Voltage                  | Vth      | ID = 1.0 mA, VDS = 10 V                   | 0.4 | 0.85 | 1.3 | V    |
| Drain-source On-state Resistance <sup>*1</sup> | RDS(on)1 | ID = 1.0 A, VGS = 4.0 V                   |     | 80   | 105 | mΩ   |
|                                                | RDS(on)2 | ID = 0.5 A, VGS = 2.5 V                   |     | 100  | 150 |      |
|                                                | RDS(on)3 | ID = 0.5 A, VGS = 1.8 V                   |     | 170  | 300 |      |
| Forward Transfer Admittance <sup>*1</sup>      | Yfs      | ID = 1.0 A, VDS = 10 V                    | 2.4 | 4.0  |     | S    |
| Input Capacitance                              | Ciss     | VDS = 10 V, VGS = 0 V, f = 1 MHz          |     | 280  |     | pF   |
| Output Capacitance                             | Coss     |                                           |     | 18   |     |      |
| Reverse Transfer Capacitance                   | Crss     |                                           |     | 17   |     |      |
| Turn-on delay time <sup>*2</sup>               | td(on)   | VDD = 10 V, VGS = 0 to 4 V,<br>ID = 1.0 A |     | 5    |     | ns   |
| Rise time <sup>*2</sup>                        | tr       |                                           |     | 8    |     |      |
| Turn-off delay time <sup>*2</sup>              | td(off)  | VDD = 10 V, VGS = 4 to 0 V,<br>ID = 1.0 A |     | 20   |     |      |
| Fall time <sup>*2</sup>                        | tf       |                                           |     | 18   |     |      |

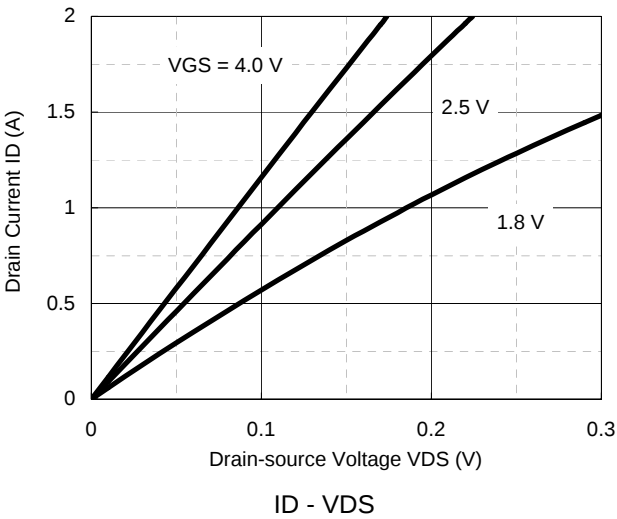
Note: Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

\*1 Pulse measurement.

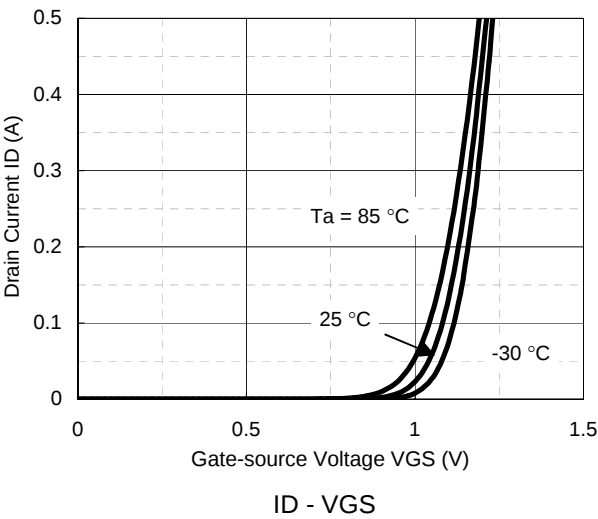
\*2 See Test circuit.

\*2 Test circuit

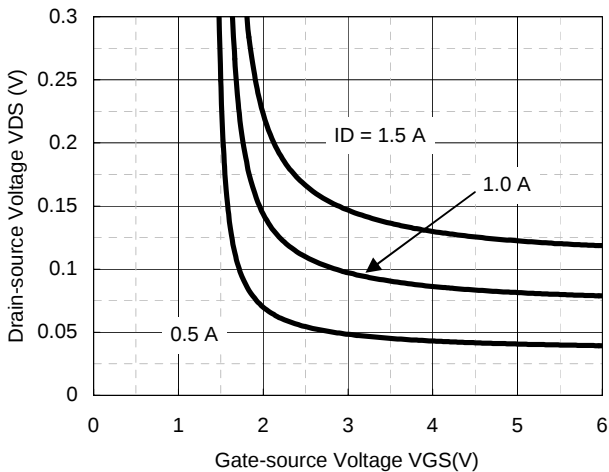




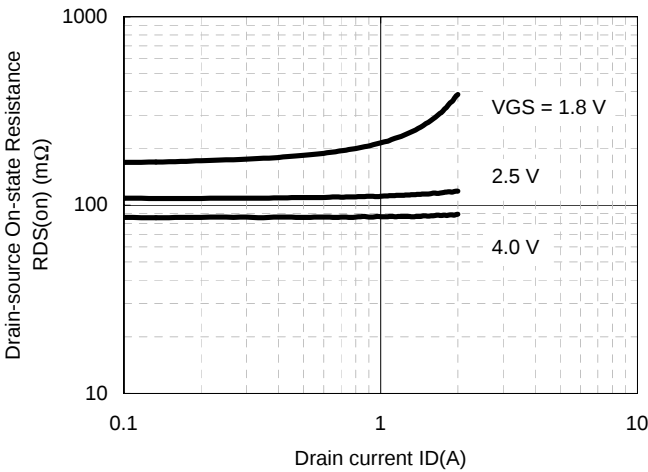
ID - VDS



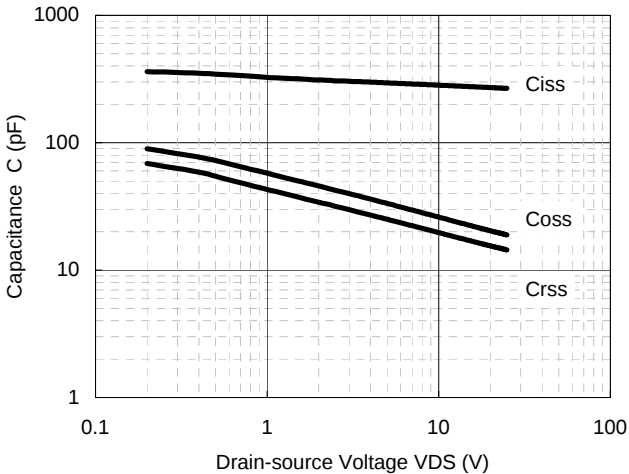
ID - VGS



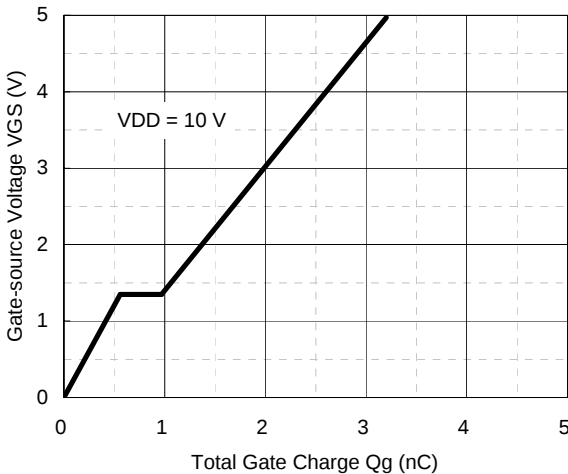
VDS - VGS



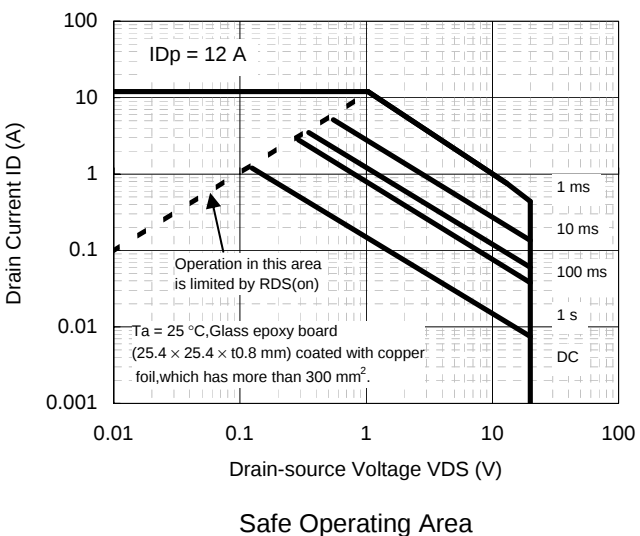
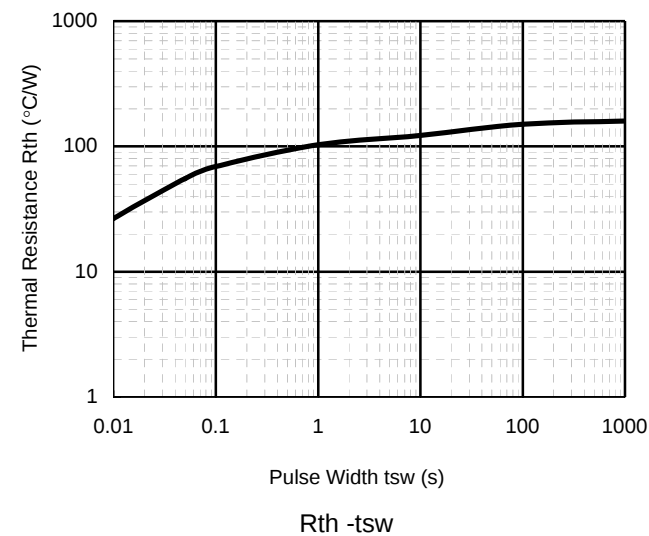
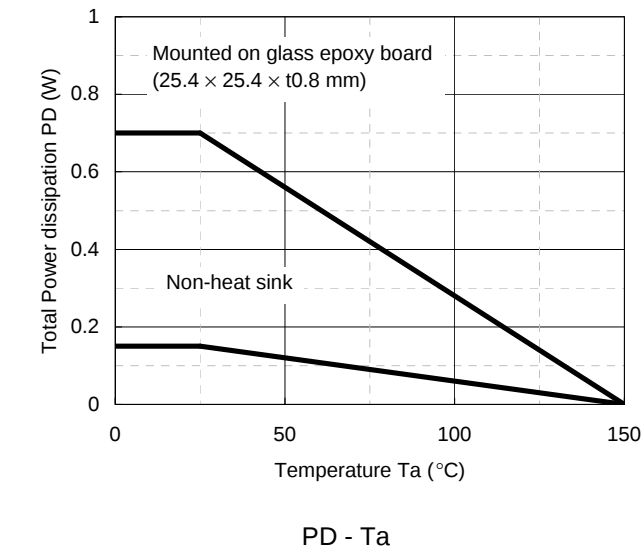
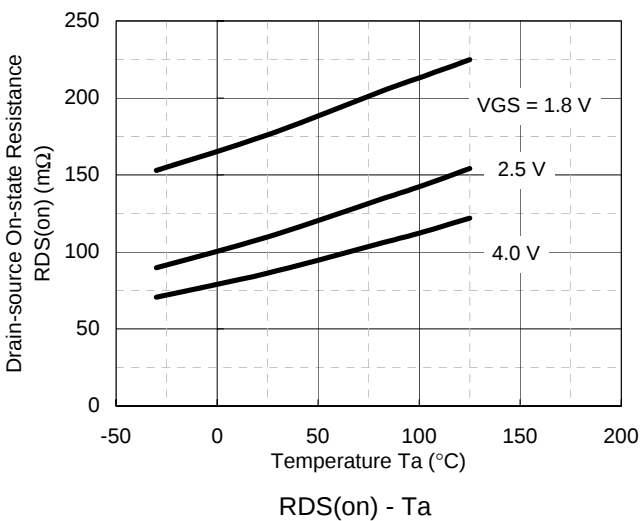
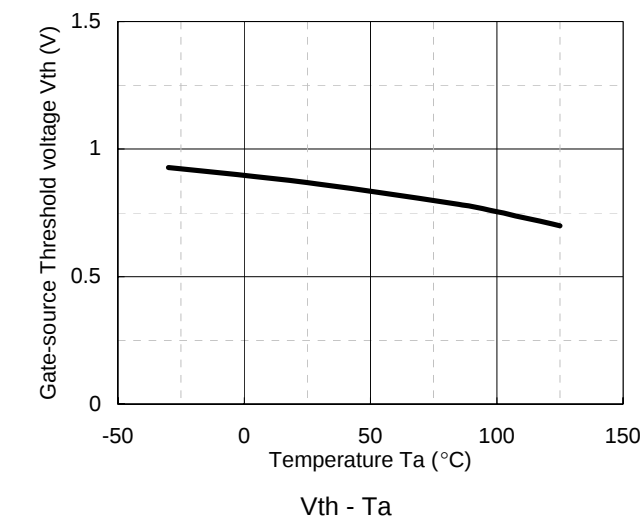
RDS(on) - ID



Capacitance - VDS

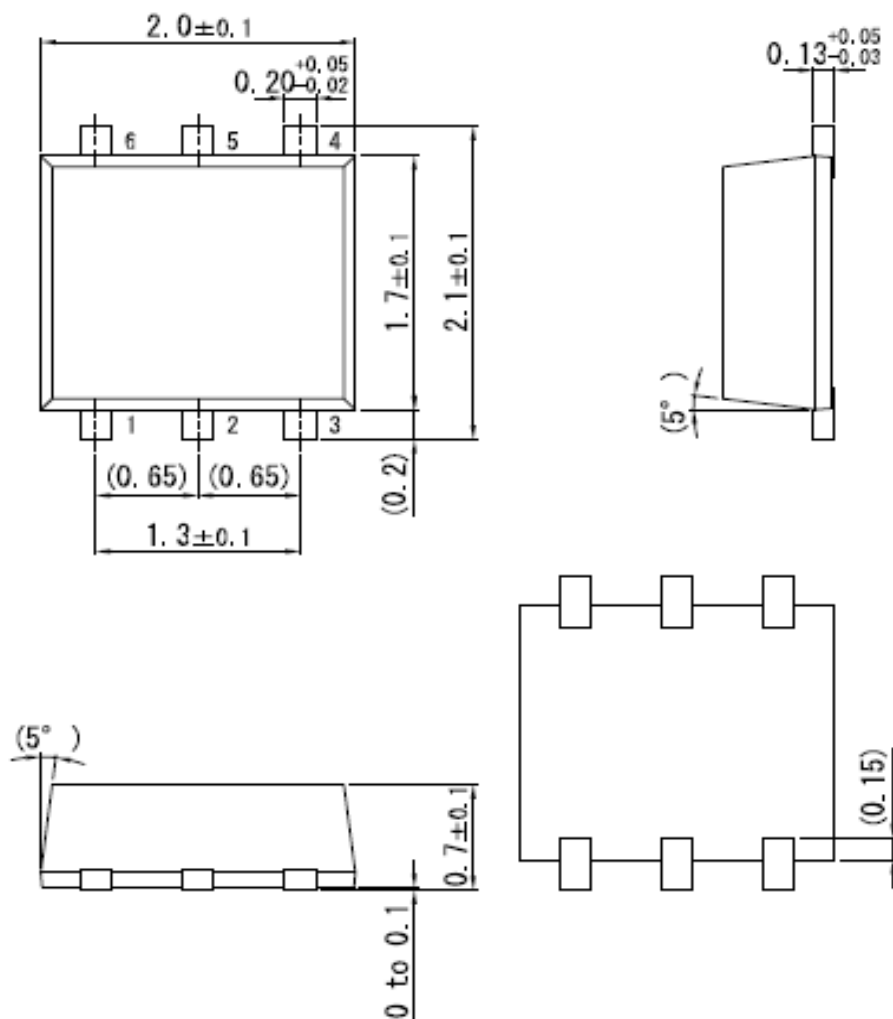


Dynamic Input/Output Characteristics

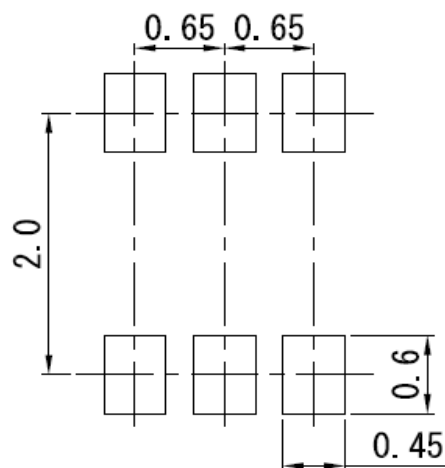


## WSMini6-F1-B

Unit: mm



## ■ Land Pattern (Reference) (Unit: mm)



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